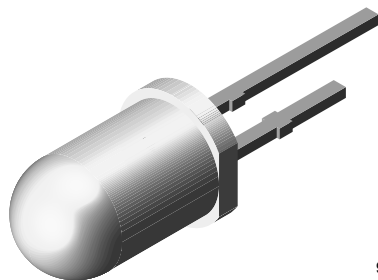




High Speed Infrared Emitting Diode, 890 nm, GaAlAs Double Hetero



94 8390

DESCRIPTION

V612P is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 890$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 10^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: $f_c = 12$ MHz
- Good spectral matching to Si photodetectors
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
GREEN
(5-2008)

APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK / FSK - coded, 450 kHz or 1.3 MHz)

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
V612P	130 to 230	± 10	890	30

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
V612P-MS21	Tape and reel	MOQ: 5000 pcs, 1000 pcs/reel	T-1 $\frac{3}{4}$

Note

- MOQ: minimum order quantity



ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100\text{ }\mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100\text{ }\mu\text{s}$	I_{FSM}	1.5	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	-40 to +85	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-40 to +100	$^{\circ}\text{C}$
Soldering temperature	$t \leq 5\text{ s}$, 2 mm from case	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction / ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

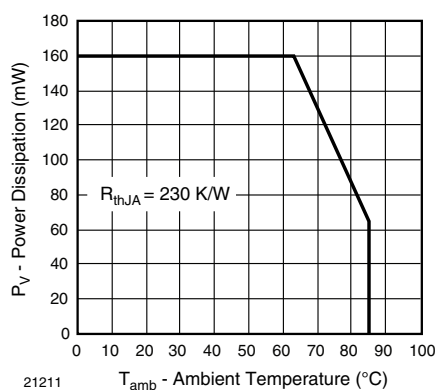


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

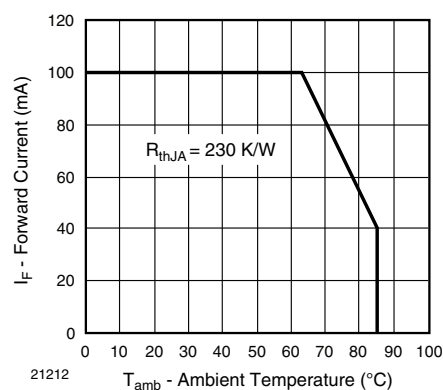


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F	-	1.4	1.6	V
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F	-	2.3	-	V
Temperature coefficient of V_F	$I_F = 1\text{ mA}$	TK_{V_F}	-	-1.8	-	mV/K
Reverse current	$V_R = 5\text{ V}$	I_R	-	-	10	μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_j	-	125	-	pF
Radiant intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_e	130	-	230	mW/sr
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e	-	1800	-	mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e	-	50	-	mW
Temperature coefficient of ϕ_e	$I_F = 100\text{ mA}$	TK_{ϕ_e}	-	-0.35	-	%/K
Angle of half intensity		φ	-	± 10	-	deg
Peak wavelength	$I_F = 100\text{ mA}$	λ_p	-	890	-	nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$	-	40	-	nm
Temperature coefficient of λ_p	$I_F = 100\text{ mA}$	TK_{λ_p}	-	0.25	-	nm/K
Rise time	$I_F = 100\text{ mA}$	t_r	-	30	-	ns
Fall time	$I_F = 100\text{ mA}$	t_f	-	30	-	ns
Cut-off frequency	$I_{DC} = 70\text{ mA}$, $I_{AC} = 30\text{ mA pp}$	f_c	-	12	-	MHz
Virtual source diameter		d	-	3.7	-	mm



BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

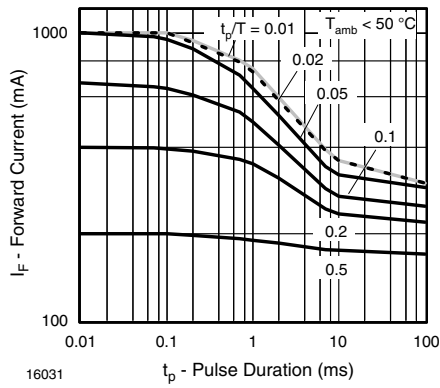


Fig. 3 - Pulse Forward Current vs. Pulse Duration

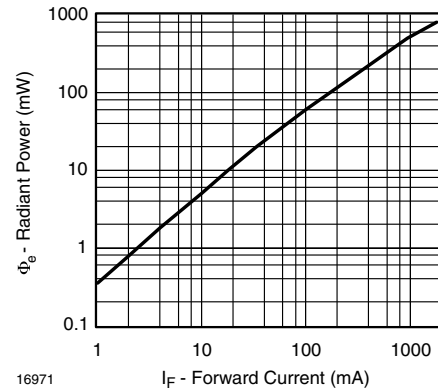


Fig. 6 - Radiant Power vs. Forward Current

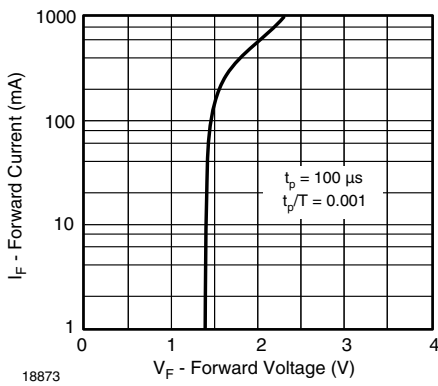


Fig. 4 - Forward Current vs. Forward Voltage

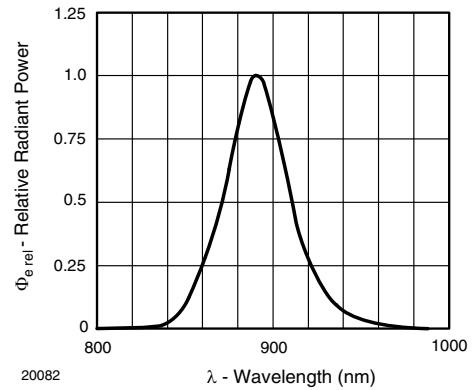


Fig. 7 - Relative Radiant Power vs. Wavelength

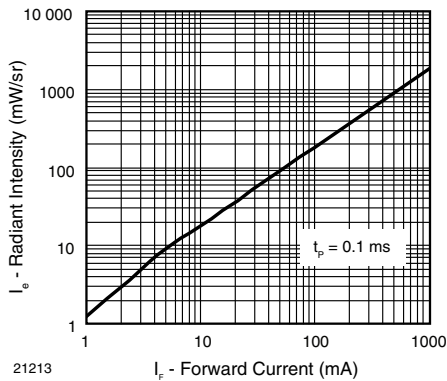


Fig. 5 - Radiant Intensity vs. Forward Current

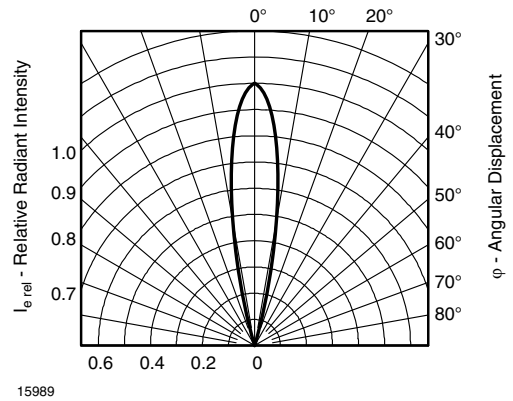
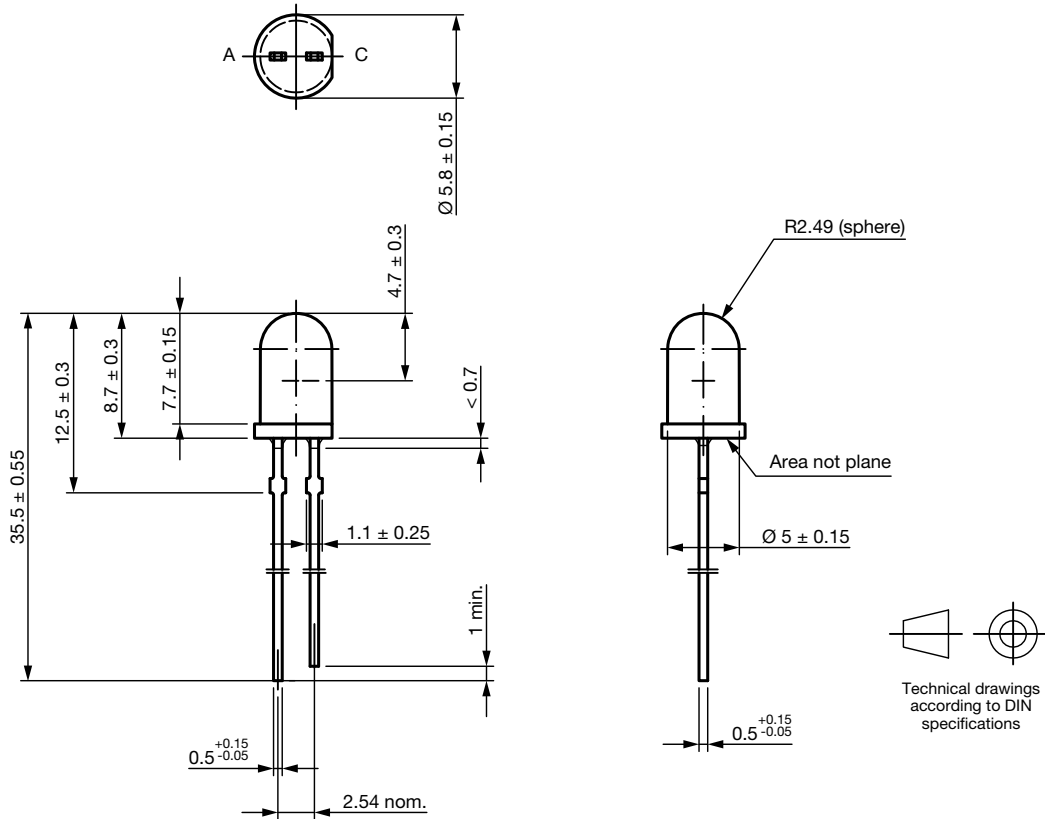


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



PACKAGE DIMENSIONS in millimeters



Technical drawings according to DIN specifications

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